

P-Channel 12-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
- 12	0.085 at $V_{GS} = - 4.5$ V	- 3.3
	0.115 at $V_{GS} = - 2.5$ V	- 2.9
	0.160 at $V_{GS} = - 1.8$ V	- 2.4

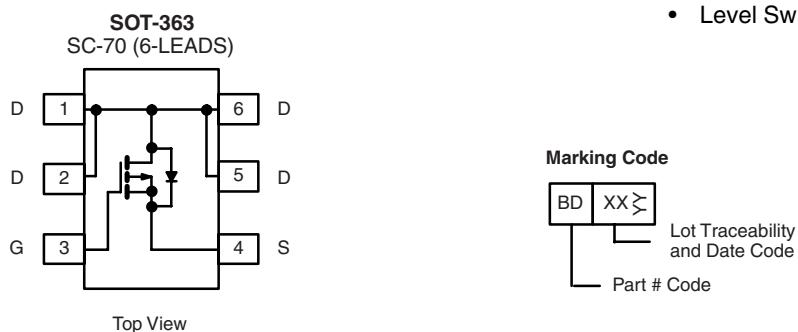
FEATURES

- TrenchFET® Power MOSFETs: 1.8 V Rated
- Thermally Enhanced SC-70 Package


RoHS*
COMPLIANT

APPLICATIONS

- Load Switching
- PA Switch
- Level Switch



Ordering Information: Si1417DH-T1
Si1417DH-T1-E3 (Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted						
Parameter		Symbol	5 sec	Steady State	Unit	
Drain-Source Voltage	$T_A = 25$ °C	V_{DS}	- 12		V	
Gate-Source Voltage		V_{GS}	± 8			
Continuous Drain Current ($T_J = 150$ °C) ^a	$T_A = 25$ °C	I_D	- 3.3	- 2.7	A	
	$T_A = 85$ °C		- 2.4	- 1.9		
Pulsed Drain Current		I_{DM}	- 8			
Continuous Diode Current (Diode Conduction) ^a		I_S	- 1.4	- 0.9		
Maximum Power Dissipation ^a	$T_A = 25$ °C	P_D	1.56	1.0	W	
	$T_A = 85$ °C		0.81	0.52		
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 5$ sec	R_{thJA}	60	80	°C/W
	Steady State		100	125	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	34	45	

Notes:

a. Surface Mounted on 1" x 1" FR4 Board.

* Pb containing terminations are not RoHS compliant, exemptions may apply.

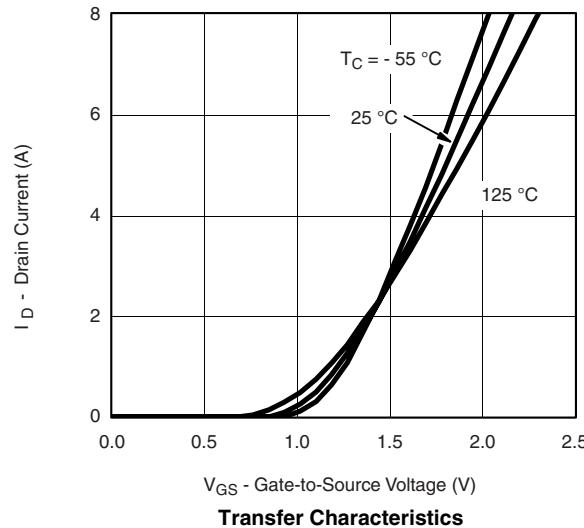
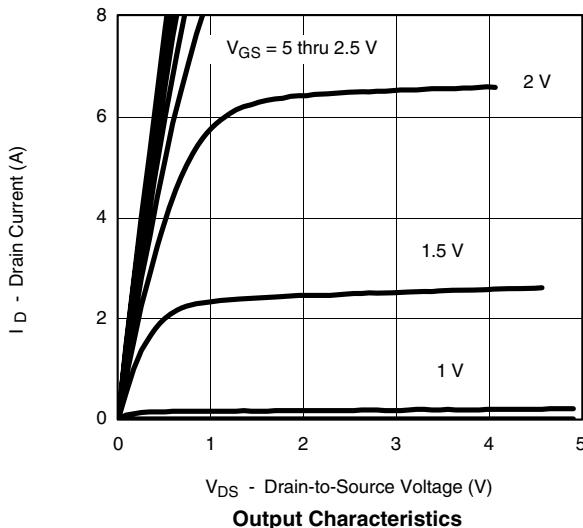
SPECIFICATIONS $T_J = 25^\circ\text{C}$, unless otherwise noted

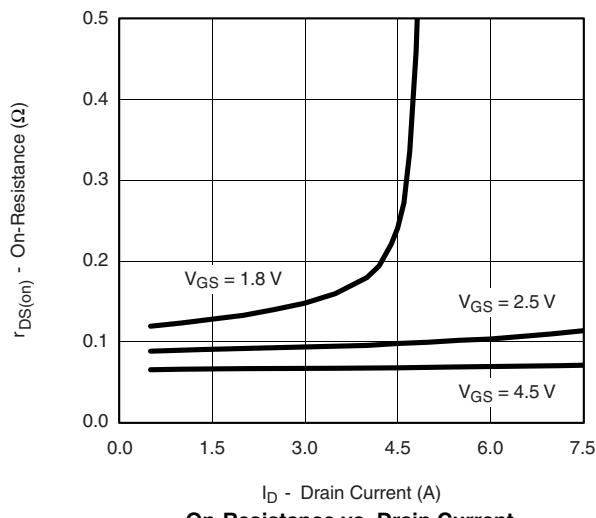
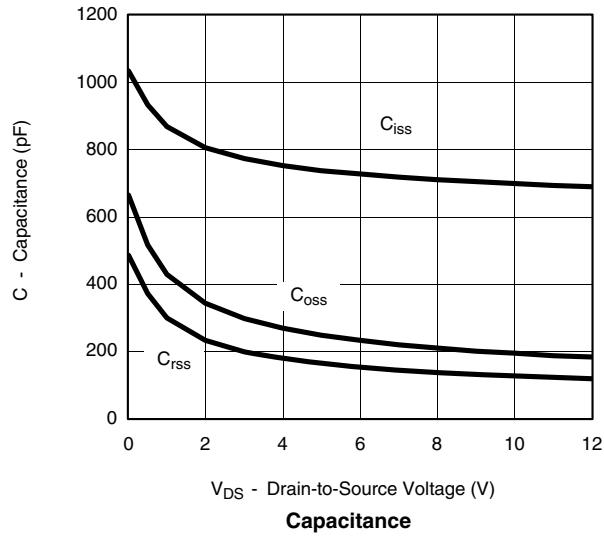
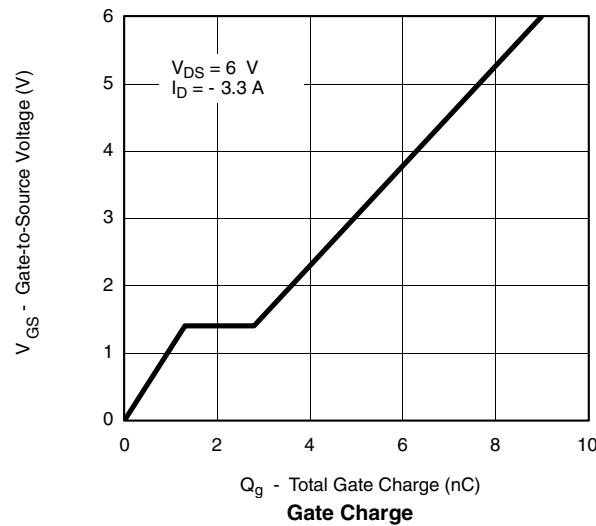
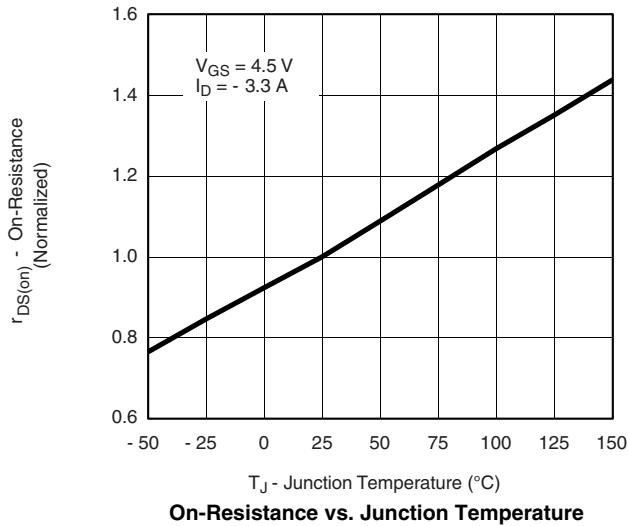
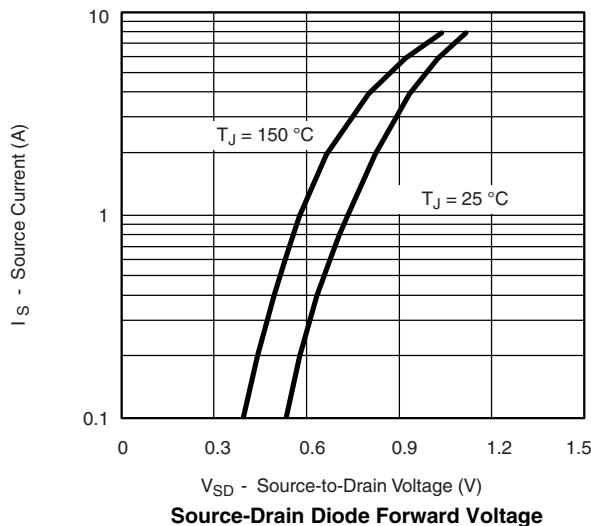
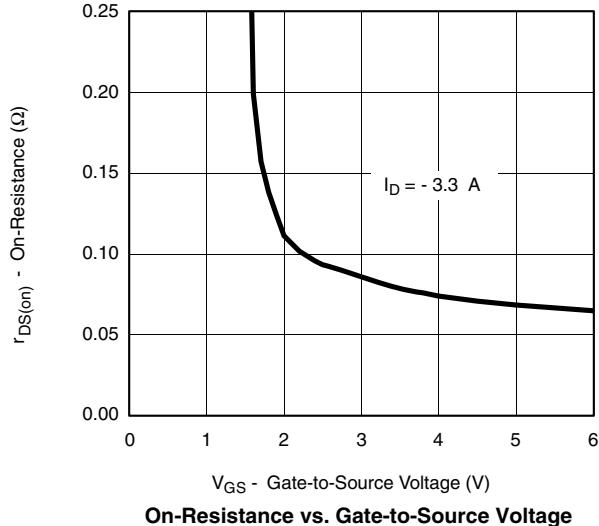
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$, $I_D = -250 \mu\text{A}$	- 0.45		- 0.8	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}$, $V_{GS} = \pm 8 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -9.6 \text{ V}$, $V_{GS} = 0 \text{ V}$		- 1		μA
		$V_{DS} = -9.6 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_J = 85^\circ\text{C}$		- 5		
On-State Drain Current ^a	$I_{D(\text{on})}$	$V_{DS} = -5 \text{ V}$, $V_{GS} = -4.5 \text{ V}$	- 4			A
Drain-Source On-State Resistance ^a	$r_{DS(\text{on})}$	$V_{GS} = -4.5 \text{ V}$, $I_D = -3.3 \text{ A}$		0.070	0.085	Ω
		$V_{GS} = -2.5 \text{ V}$, $I_D = -2.9 \text{ A}$		0.095	0.115	
		$V_{GS} = -1.8 \text{ V}$, $I_D = -1.0 \text{ A}$		0.133	0.160	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10 \text{ V}$, $I_D = -3.3 \text{ A}$		8		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -1.4 \text{ A}$, $V_{GS} = 0 \text{ V}$		- 0.80	- 1.1	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -6 \text{ V}$, $V_{GS} = -4.5 \text{ V}$, $I_D = -3.3 \text{ A}$		7.0	10.5	nC
Gate-Source Charge	Q_{gs}			1.3		
Gate-Drain Charge	Q_{gd}			1.5		
Turn-On Delay Time	$t_{d(\text{on})}$	$V_{DD} = -6 \text{ V}$, $R_L = 6 \Omega$ $I_D \geq -1 \text{ A}$, $V_{GEN} = -4.5 \text{ V}$, $R_G = 6 \Omega$		18	30	ns
Rise Time	t_r			28	45	
Turn-Off Delay Time	$t_{d(\text{off})}$			41	65	
Fall Time	t_f			60	90	

Notes:

a. Pulse test; pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

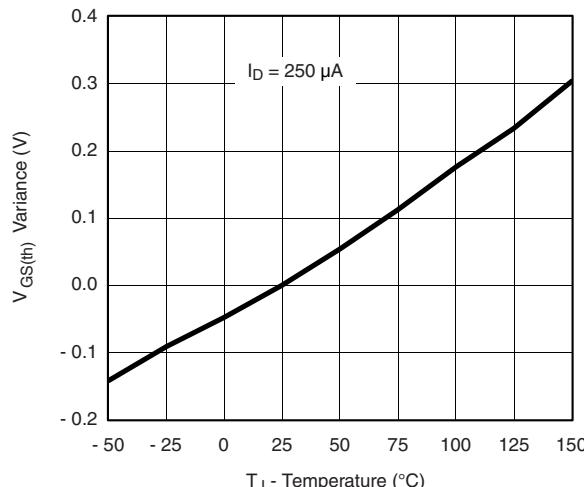
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25°C , unless otherwise noted


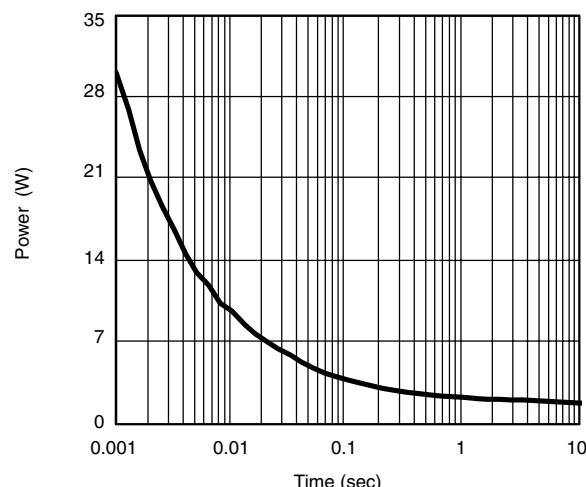
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On-Resistance vs. Drain Current

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

Si1417DH

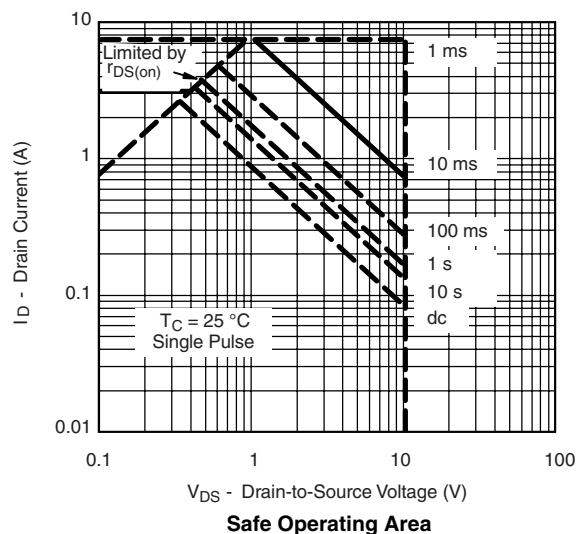
Vishay Siliconix

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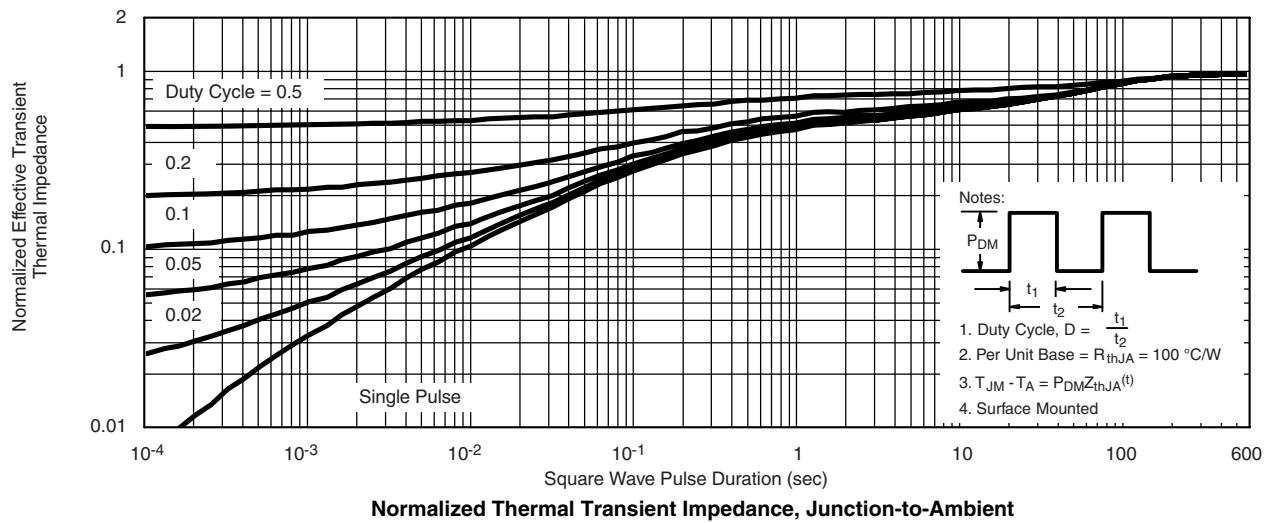
Threshold Voltage



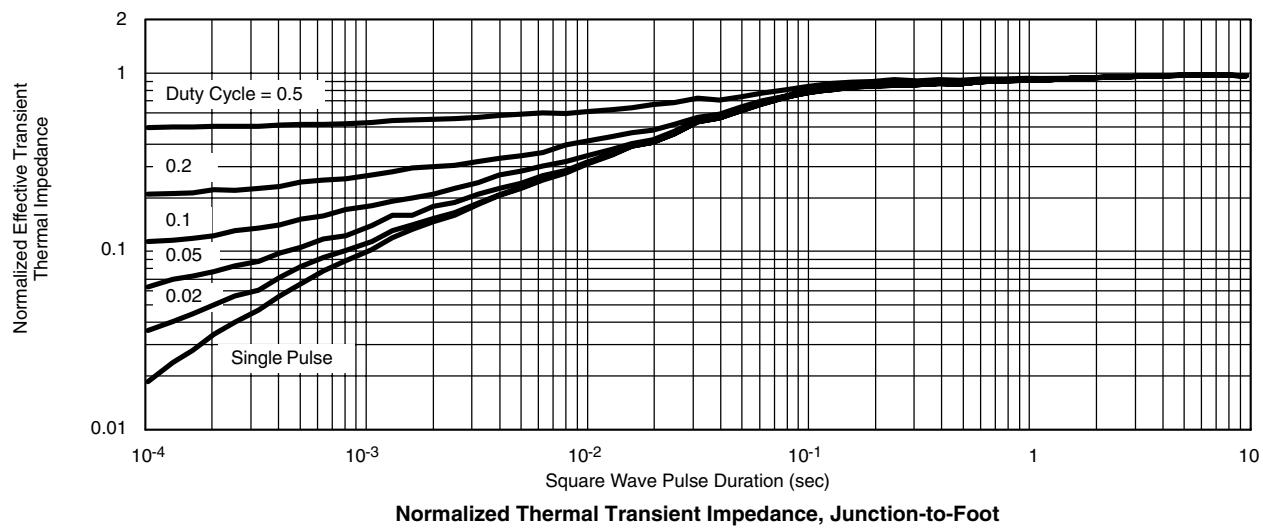
Single Pulse Power, Junction-to-Ambient



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

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